

# MMBT4403WT1G

## Switching Transistor

### PNP Silicon

#### Features

- Moisture Sensitivity Level: 1
- ESD Rating: Human Body Model; 4 kV,  
Machine Model; 400 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	–40	Vdc
Collector–Base Voltage	$V_{CBO}$	–40	Vdc
Emitter–Base Voltage	$V_{EBO}$	–5.0	Vdc
Collector Current – Continuous	$I_C$	–600	mAdc

#### THERMAL CHARACTERISTICS

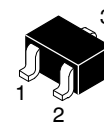
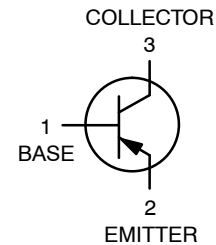
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board $T_A = 25^\circ\text{C}$	$P_D$	150	mW
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



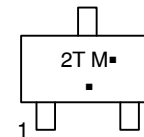
ON Semiconductor®

<http://onsemi.com>



SC-70  
CASE 419  
STYLE 3

#### MARKING DIAGRAM



2T = Specific Device Code  
M = Date Code  
■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT4403WT1G	SC-70 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBT4403WT1G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage (Note 1) (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-40	-	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = -0.1 mAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-40	-	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = -0.1 mAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	-5.0	-	Vdc
Base Cutoff Current (V <sub>CE</sub> = -35 Vdc, V <sub>EB</sub> = -0.4 Vdc)	I <sub>BEV</sub>	-	-0.1	μAdc
Collector Cutoff Current (V <sub>CE</sub> = -35 Vdc, V <sub>EB</sub> = -0.4 Vdc)	I <sub>CEX</sub>	-	-0.1	μAdc

## ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = -0.1 mAdc, V <sub>CE</sub> = -1.0 Vdc) (I <sub>C</sub> = -1.0 mAdc, V <sub>CE</sub> = -1.0 Vdc) (I <sub>C</sub> = -10 mAdc, V <sub>CE</sub> = -1.0 Vdc) (I <sub>C</sub> = -150 mAdc, V <sub>CE</sub> = -2.0 Vdc) (Note 1) (I <sub>C</sub> = -500 mAdc, V <sub>CE</sub> = -2.0 Vdc) (Note 1)	h <sub>FE</sub>	30 60 100 100 20	- - - 300 -	-
Collector-Emitter Saturation Voltage (Note 1) (I <sub>C</sub> = -150 mAdc, I <sub>B</sub> = -15 mAdc) (I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)	V <sub>CE(sat)</sub>	- -	-0.4 -0.75	Vdc
Base-Emitter Saturation Voltage (Note 1) (I <sub>C</sub> = -150 mAdc, I <sub>B</sub> = -15 mAdc) (I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)	V <sub>BE(sat)</sub>	-0.75 -	-0.95 -1.3	Vdc

## SMALL-SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product (I <sub>C</sub> = -20 mAdc, V <sub>CE</sub> = -10 Vdc, f = 100 MHz)	f <sub>T</sub>	200	-	MHz
Collector-Base Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>cb</sub>	-	8.5	pF
Emitter-Base Capacitance (V <sub>BE</sub> = -0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>eb</sub>	-	30	pF
Input Impedance (I <sub>C</sub> = -1.0 mAdc, V <sub>CE</sub> = -10 Vdc, f = 1.0 kHz)	h <sub>ie</sub>	1.5	15	kΩ
Voltage Feedback Ratio (I <sub>C</sub> = -1.0 mAdc, V <sub>CE</sub> = -10 Vdc, f = 1.0 kHz)	h <sub>re</sub>	0.1	8.0	X 10 <sup>-4</sup>
Small-Signal Current Gain (I <sub>C</sub> = -1.0 mAdc, V <sub>CE</sub> = -10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	60	500	-
Output Admittance (I <sub>C</sub> = -1.0 mAdc, V <sub>CE</sub> = -10 Vdc, f = 1.0 kHz)	h <sub>oe</sub>	1.0	100	μmhos

## SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = -30 Vdc, V <sub>EB</sub> = -2.0 Vdc, I <sub>C</sub> = -150 mAdc, I <sub>B1</sub> = -15 mAdc)	t <sub>d</sub>	-	15	ns
Rise Time		t <sub>r</sub>	-	20	
Storage Time	(V <sub>CC</sub> = -30 Vdc, I <sub>C</sub> = -150 mAdc, I <sub>B1</sub> = I <sub>B2</sub> = -15 mAdc)	t <sub>s</sub>	-	225	ns
Fall Time		t <sub>f</sub>	-	30	

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

## SWITCHING TIME EQUIVALENT TEST CIRCUIT

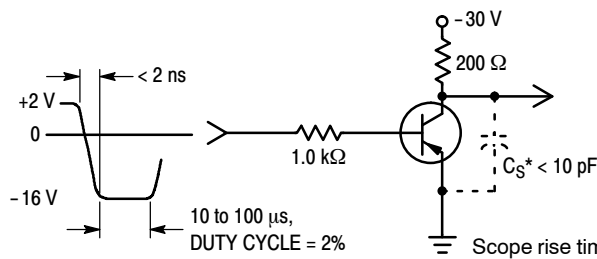


Figure 1. Turn-On Time

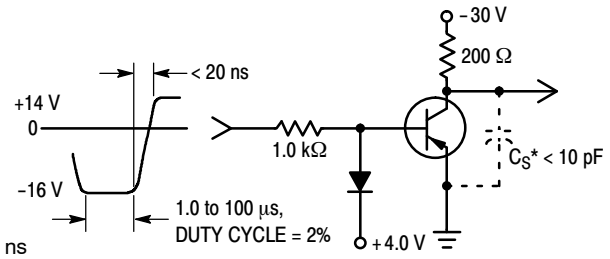


Figure 2. Turn-Off Time

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## TRANSIENT CHARACTERISTICS

— 25°C    - - - 100°C

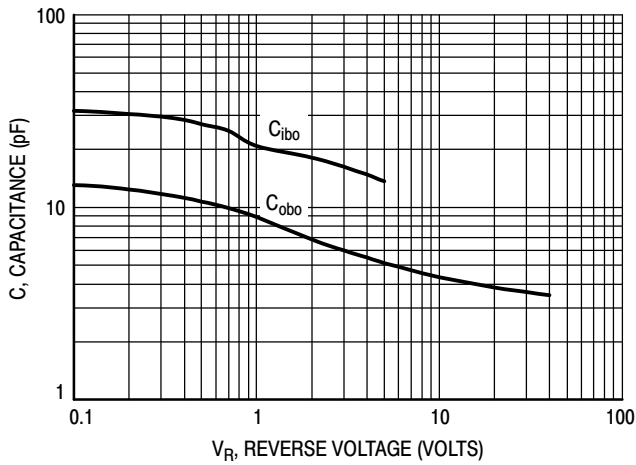


Figure 3. Capacitances

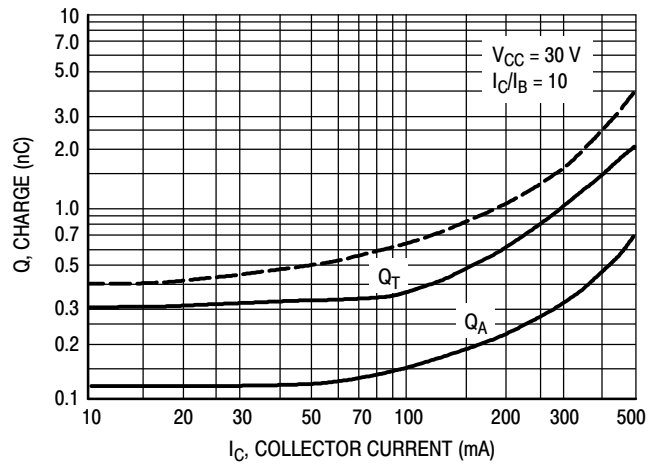


Figure 4. Charge Data

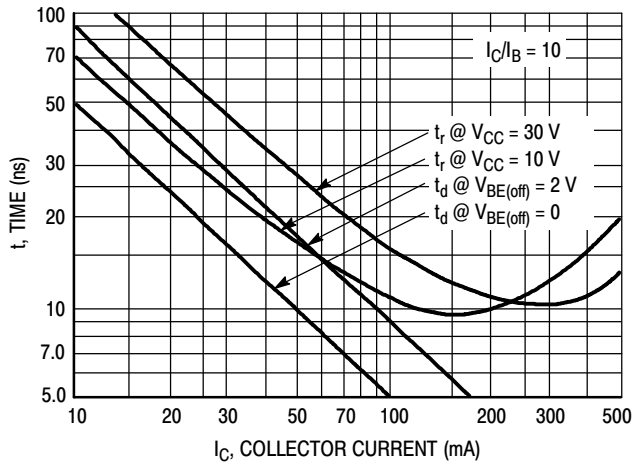


Figure 5. Turn-On Time

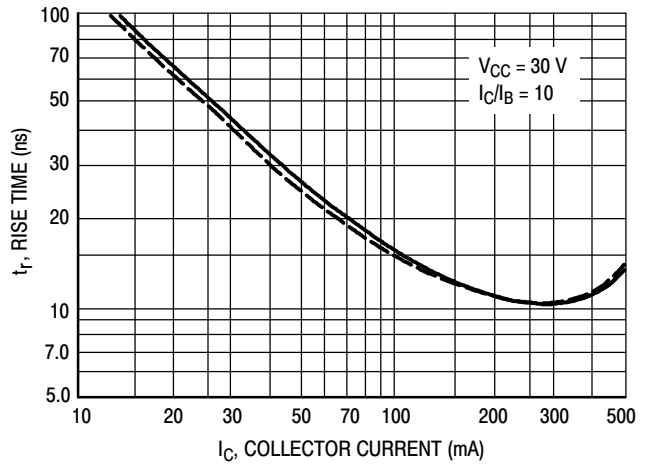


Figure 6. Rise Time

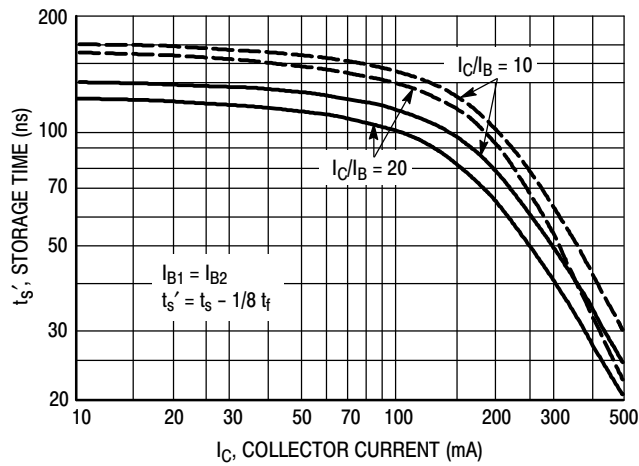


Figure 7. Storage Time

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## SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

$V_{CE} = -10 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ ; Bandwidth = 1.0 Hz

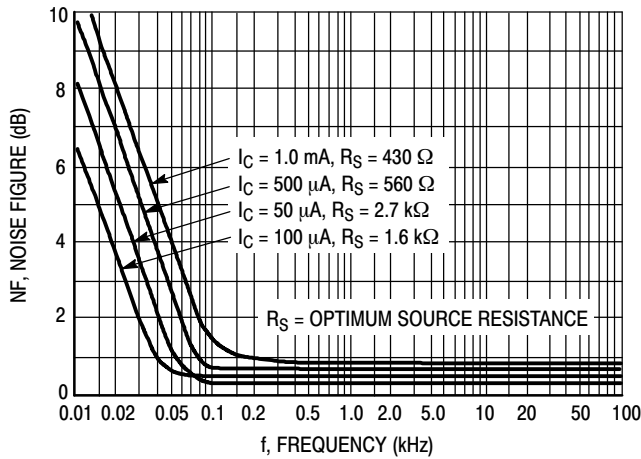


Figure 8. Frequency Effects

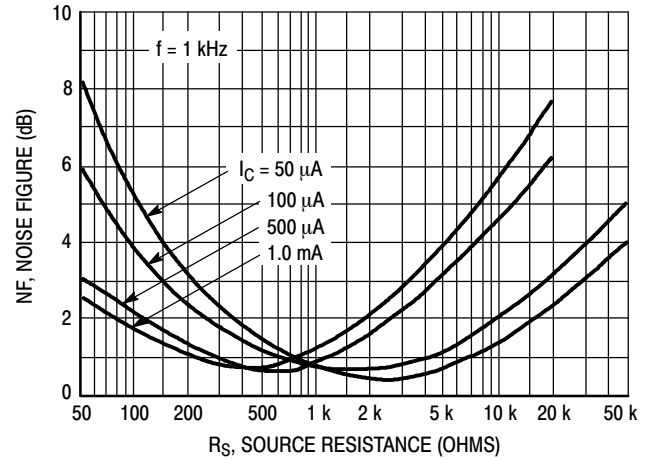


Figure 9. Source Resistance Effects

## h PARAMETERS

$V_{CE} = 10 \text{ Vdc}$ ,  $f = 1.0 \text{ kHz}$ ,  $T_A = 25^\circ\text{C}$

This group of graphs illustrates the relationship between  $h_{fe}$  and other “h” parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4403WT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

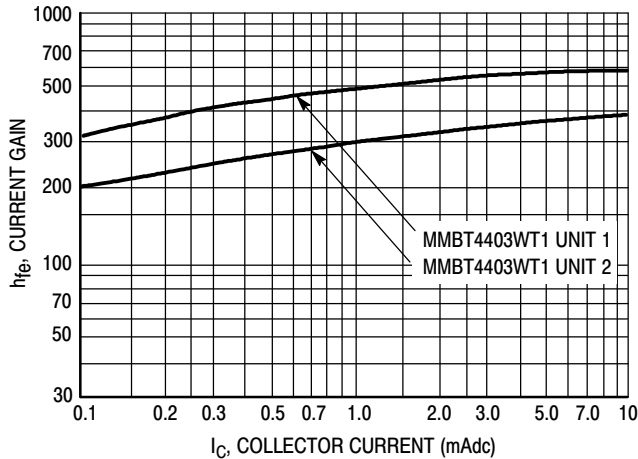


Figure 10. Current Gain

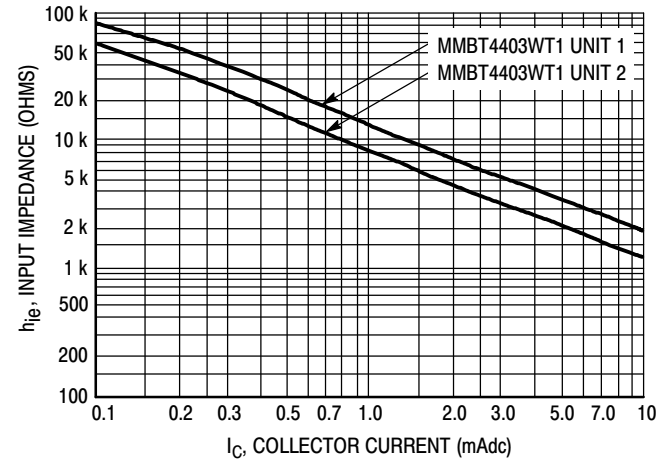


Figure 11. Input Impedance

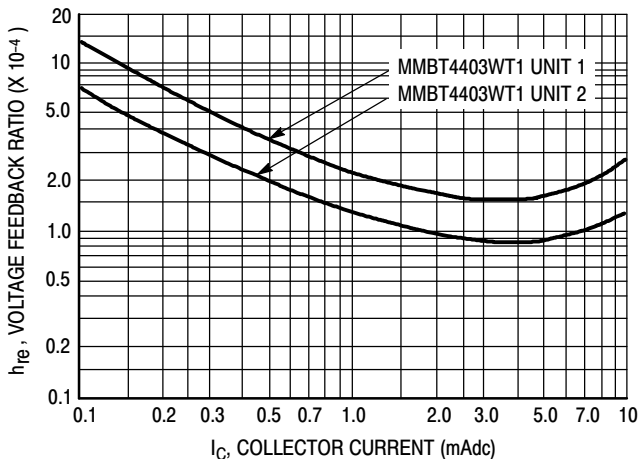


Figure 12. Voltage Feedback Ratio

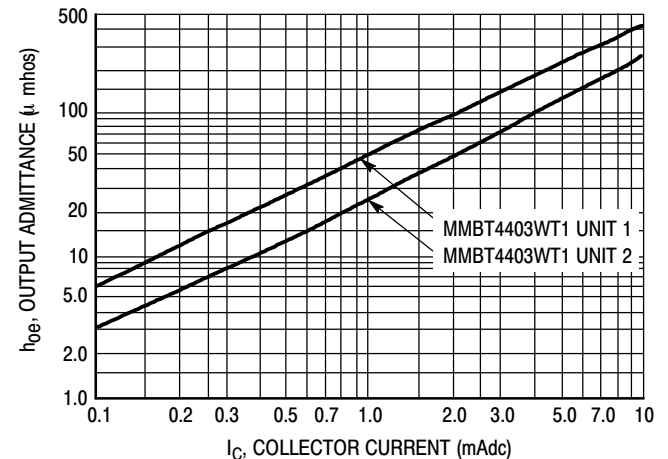
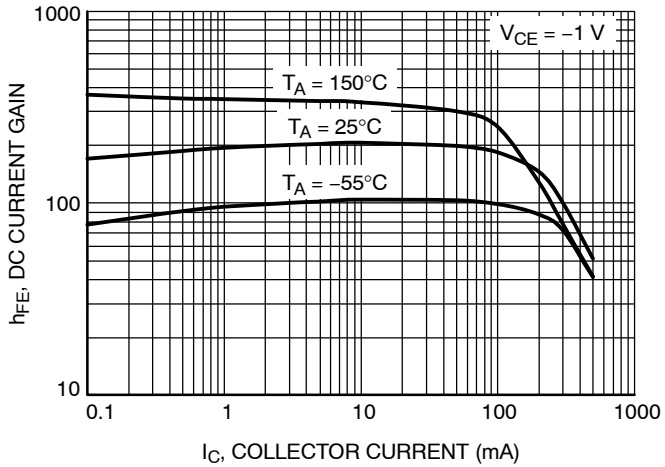


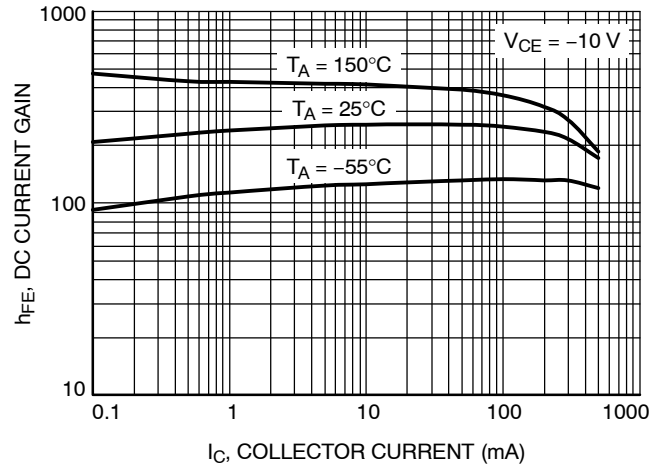
Figure 13. Output Admittance

# MMBT4403WT1G

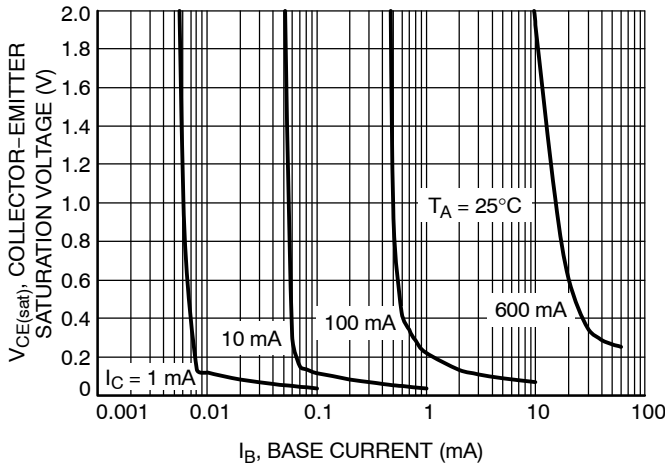
## STATIC CHARACTERISTICS



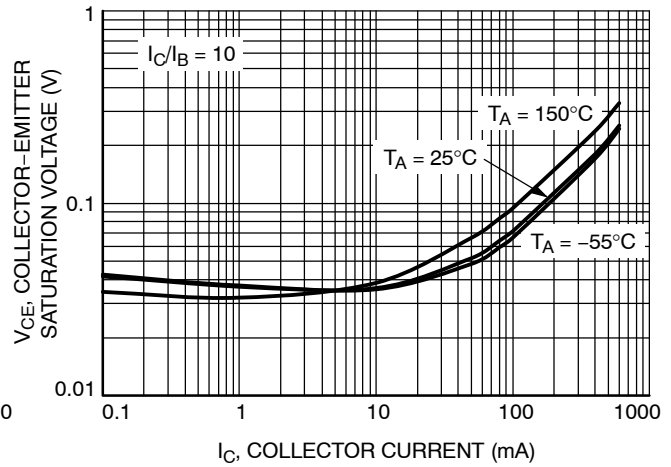
**Figure 14. DC Current Gain vs. Collector Current**



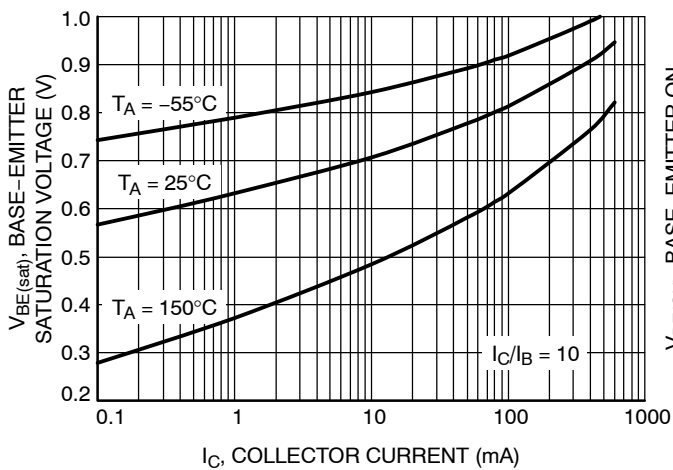
**Figure 15. DC Current Gain vs. Collector Current**



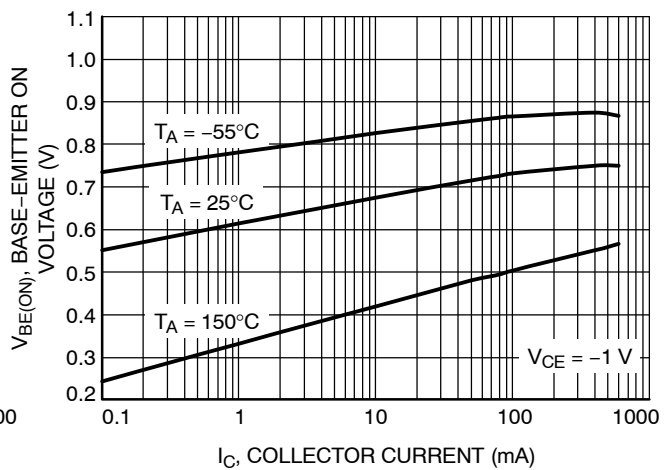
**Figure 16. Saturation Region**



**Figure 17. Collector Emitter Saturation Voltage vs. Collector Current**



**Figure 18. Base Emitter Saturation Voltage vs. Collector Current**



**Figure 19. Base-Emitter Turn-On Voltage vs. Collector Current**

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## STATIC CHARACTERISTICS

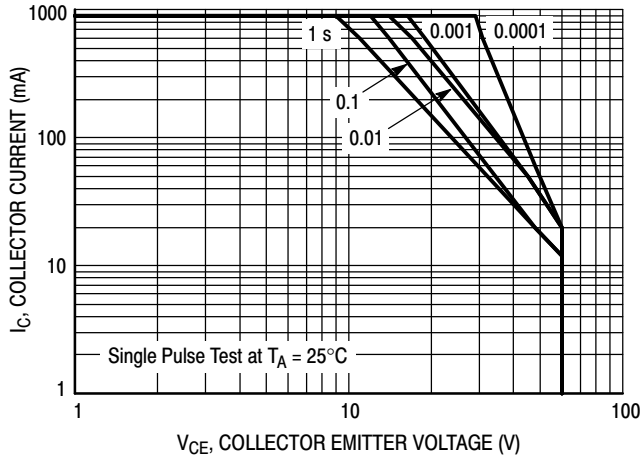


Figure 20. Safe Operating Area

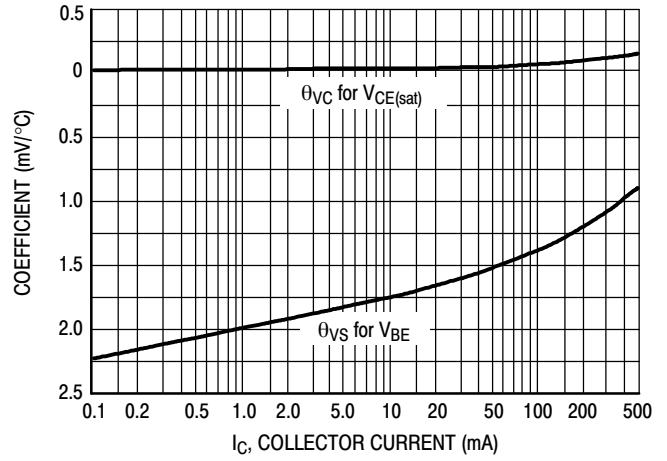


Figure 21. Temperature Coefficients

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

## SC-70 (SOT-323) CASE 419 ISSUE R

DATE 11 OCT 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

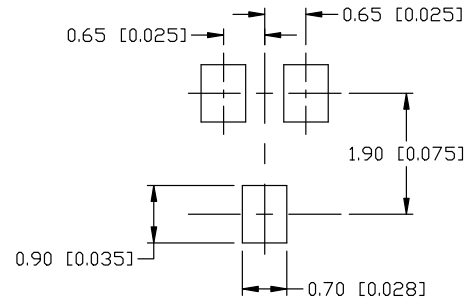
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H <sub>E</sub>	2.00	2.10	2.40	0.079	0.083	0.095

### GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

### SOLDERING FOOTPRINT

- |   |   |   |  |   |   |
|---|---|---|--|---|---|
| STYLE 1:<br>CANCELLED                                 | STYLE 2:<br>PIN 1. ANODE<br>2. N.C.<br>3. CATHODE     | STYLE 3:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE       | STYLE 5:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          |   |
| STYLE 6:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR | STYLE 7:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 8:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN      | STYLE 9:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 10:<br>PIN 1. CATHODE<br>2. ANODE<br>3. ANODE-CATHODE | STYLE 11:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE |

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